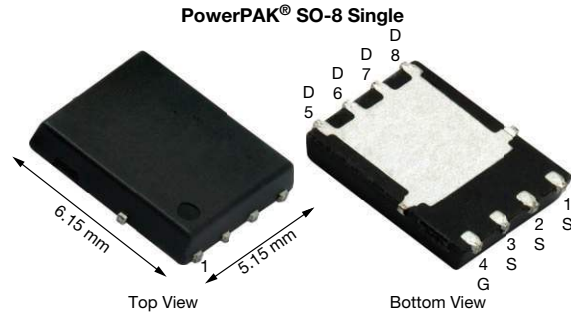


## N-Channel 200 V (D-S) MOSFET



### FEATURES

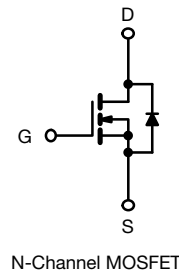
- TrenchFET® power MOSFETs
- New low thermal resistance PowerPAK® package with low 1.07 mm profile
- PWM optimized for fast switching

### APPLICATIONS

- Primary side switch



PRODUCT SUMMARY	
$V_{DS}$ (V)	200
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.130
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 6$ V	0.142
$Q_g$ typ. (nC)	20
$I_D$ (A)	4.1
Configuration	Single



ORDERING INFORMATION	
Package	PowerPAK SO-8
Lead (Pb)-free	Si7462DP-T1-E3
Lead (Pb)-free and halogen-free	Si7462DP-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)					
PARAMETER	SYMBOL	10 s	STEADY STATE	UNIT	
Drain-source voltage	$V_{DS}$	200	200	V	
Gate-source voltage	$V_{GS}$	$\pm 20$	$\pm 20$		
Continuous drain current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	4.1	2.6	A
		$T_A = 85$ °C	3	1.9	
Pulsed drain current	$I_{DM}$	12	12		
Avalanche current	$I_{AS}$	L = 0.1 mH	6	6	mJ
Single avalanche energy (duty cycle $\leq 1$ %)			$E_{AS}$	1.8	
Continuous source current (diode conduction) <sup>a</sup>	$I_S$	4	1.6	A	
Maximum power dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	4.8	1.9	W
		$T_A = 85$ °C	2.6	1	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150		°C	
Soldering recommendations (peak temperature) <sup>b, c</sup>		260			

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ s	21	26	°C/W
		Steady state	55	65	
Maximum junction-to-case (drain)	$R_{thJC}$	1.7	2.1		

### Notes

- Surface mounted on 1" x 1" FR4 board
- See solder profile ([www.vishay.com/ppg?73257](http://www.vishay.com/ppg?73257)). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	-	4	V
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 200\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 200\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 85\text{ }^\circ\text{C}$	-	-	20	
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$ , $V_{GS} = 10\text{ V}$	12	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 4.1\text{ A}$	-	0.110	0.130	$\Omega$
		$V_{GS} = 6\text{ V}$ , $I_D = 3.9\text{ A}$	-	0.120	0.142	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 4.1\text{ A}$	-	13	-	S
Diode forward voltage <sup>a</sup>	$V_{SD}$	$I_S = 4\text{ A}$ , $V_{GS} = 0\text{ V}$	-	0.8	1.2	V
<b>Dynamic <sup>b</sup></b>						
Total gate charge	$Q_g$	$V_{DS} = 100\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 4.1\text{ A}$	-	20	30	nC
Gate-source charge	$Q_{gs}$		-	4.5	-	
Gate-drain charge	$Q_{gd}$		-	6.5	-	
Gate resistance	$R_g$		-	2	-	$\Omega$
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 100\text{ V}$ , $R_L = 100\text{ }\Omega$ $I_D \cong 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 6\text{ }\Omega$	-	15	25	ns
Rise time	$t_r$		-	15	25	
Turn-off delay time	$t_{d(off)}$		-	40	60	
Fall time	$t_f$		-	20	30	
Source-drain reverse recovery time	$t_{rr}$	$I_F = 4\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	70	110	

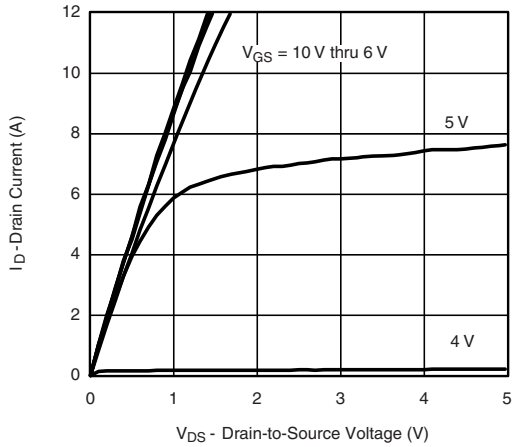
**Notes**

- a. Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

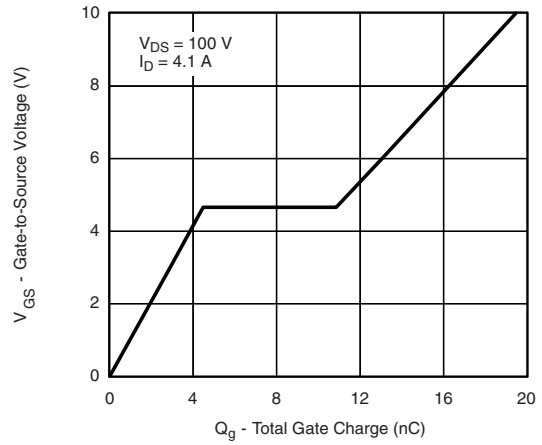
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



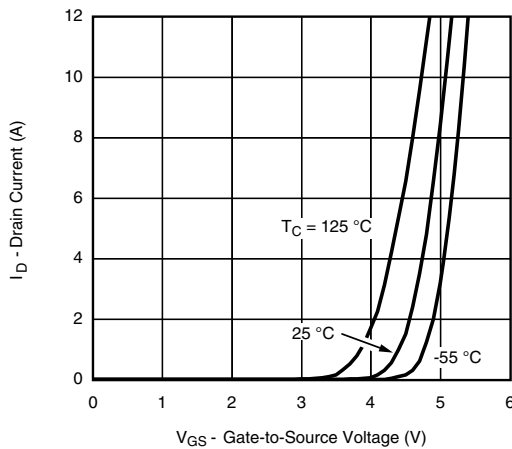
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



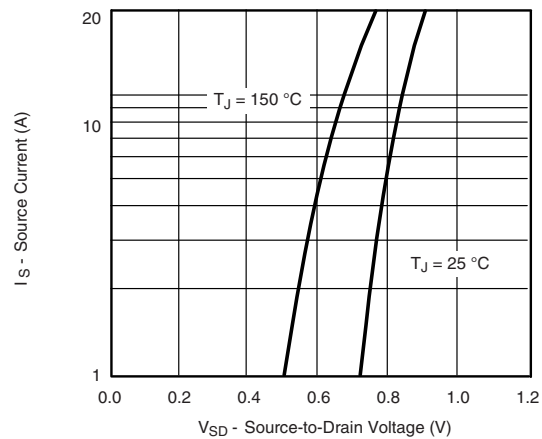
Output Characteristics



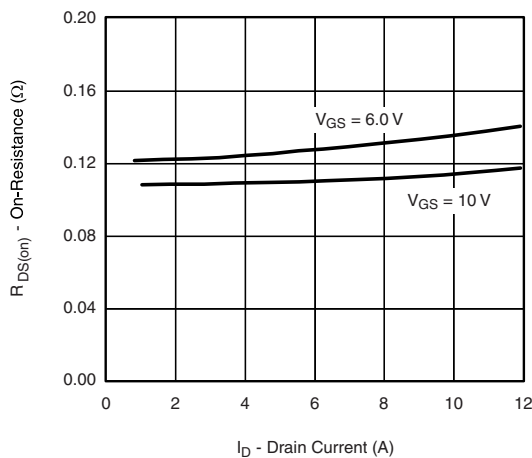
Gate Charge



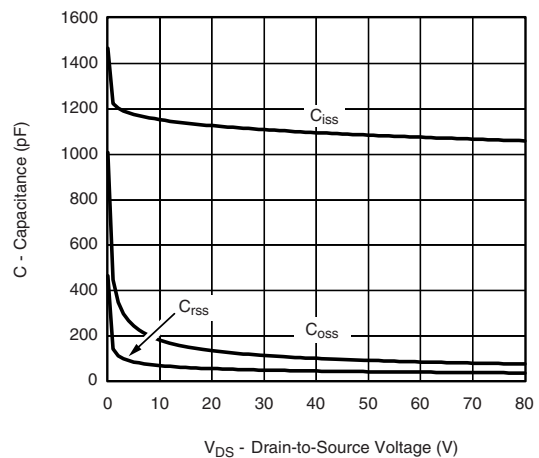
Transfer Characteristics



Source-Drain Diode Forward Voltage



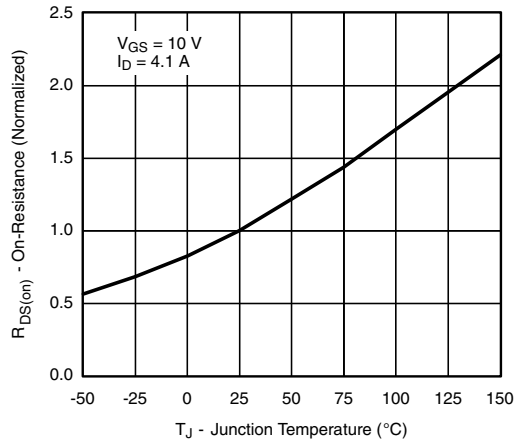
On-Resistance vs. Drain Current



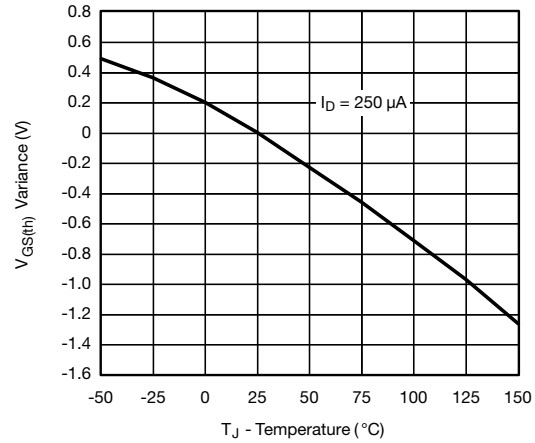
Capacitance



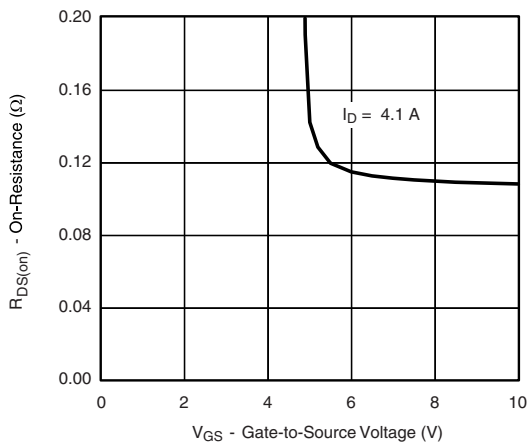
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



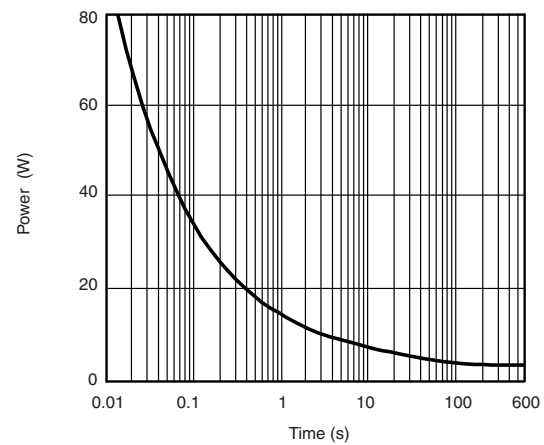
**On-Resistance vs. Junction Temperature**



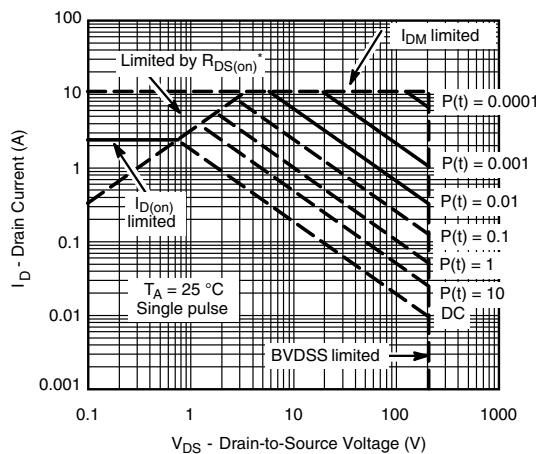
**Threshold Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



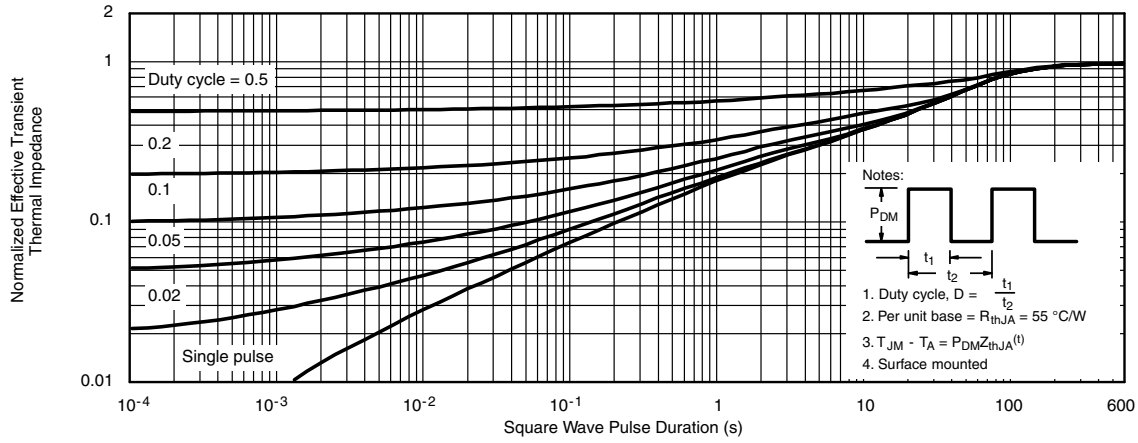
**Single Pulse Power**



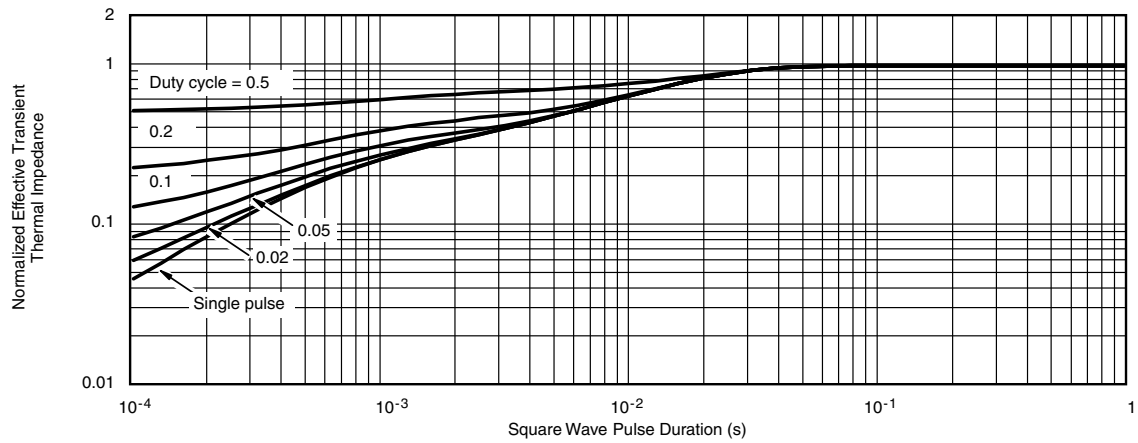
**Safe Operating Area**



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

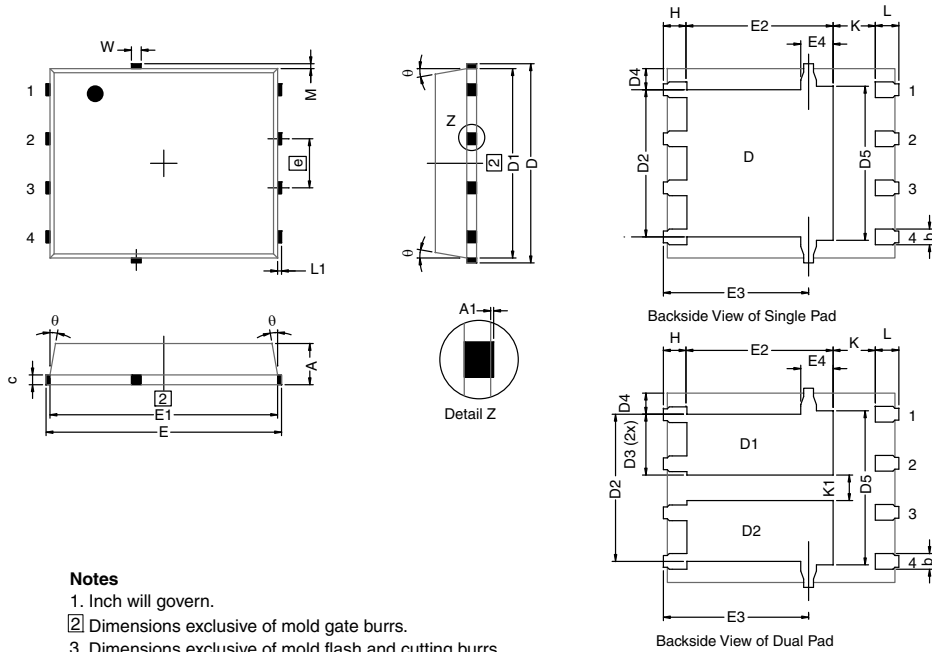


Normalized Thermal Transient Impedance, Junction-to-Case

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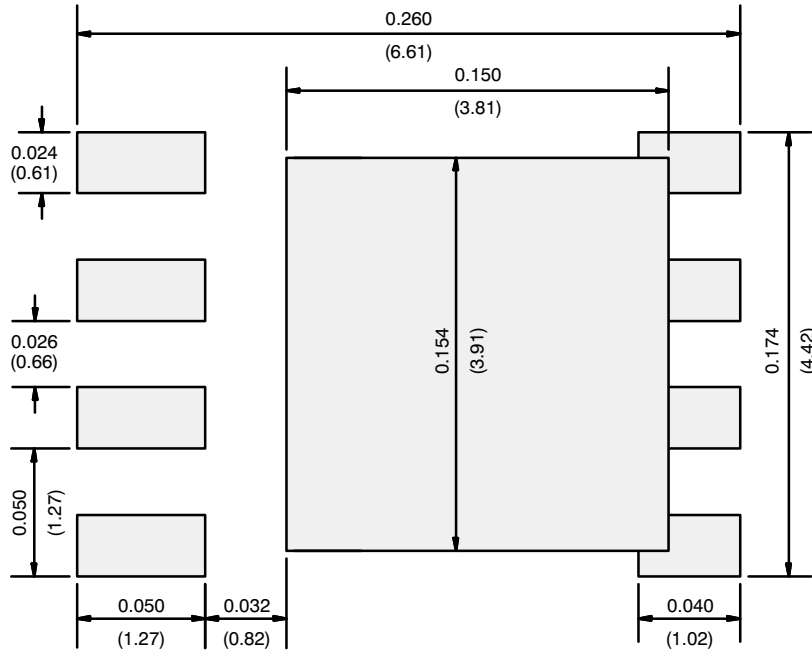


# PowerPAK<sup>®</sup> SO-8, (Single/Dual)



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1		-	0.05	0	-	0.002
b	0.33	0.41	0.51	0.013	0.016	0.020
c	0.23	0.28	0.33	0.009	0.011	0.013
D	5.05	5.15	5.26	0.199	0.203	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.56	3.76	3.91	0.140	0.148	0.154
D3	1.32	1.50	1.68	0.052	0.059	0.066
D4	0.57 typ.			0.0225 typ.		
D5	3.98 typ.			0.157 typ.		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	5.79	5.89	5.99	0.228	0.232	0.236
E2	3.48	3.66	3.84	0.137	0.144	0.151
E3	3.68	3.78	3.91	0.145	0.149	0.154
E4	0.75 typ.			0.030 typ.		
e	1.27 BSC			0.050 BSC		
K	1.27 typ.			0.050 typ.		
K1	0.56	-	-	0.022	-	-
H	0.51	0.61	0.71	0.020	0.024	0.028
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 typ.			0.005 typ.		
ECN: S17-0173-Rev. L, 13-Feb-17						
DWG: 5881						

## RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)



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